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FORM PTO-1449		SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.		CONFIRMATION NO. 3451

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	D1 3,901,423	08/1975	Hillberry, et al.		
	D2 3,915,757	10/1975	Engel		
	D3 3,957,107	05/1976	Altoz et al.		
	D4 3,993,909	11/1976	Drews et al.		
	D5 4,006,340	02/1977	Gorinas		
	D6 4,039,416	08/1977	White		
	D7 4,074,139	02/1978	Pankove		
	D8 4,107,350	08/1978	Berg et al.		
	D9 4,108,751	08/1978	King		
	D10 4,121,334	10/1978	Wallis		
	D11 4,170,662	10/1979	Weiss et al.		
	D12 4,179,324	12/1979	Kirkpatrick		
	D13 4,244,348	01/1981	Wilkes		
	D14 4,252,837	02/1981	Auton		
	D15 4,274,004	06/1981	Kanai		
	D16 4,324,631	08/1982	White et al.		
	D17 4,346,123	08/1982	Kaufmann		
	D18 4,361,600	11/1982	Brown		
	D19 4,368,083	01/1983	Bruel et al.		
	D20 4,412,868	11/1983	Brown et al.		
	D21 4,452,644	06/1984	Bruel et al.		
	D22 4,468,309	08/1984	White		
	D23 4,471,003	09/1984	Cann		
	D24 4,486,247	12/1984	Ecer et al.		
	D25 4,490,190	12/1984	Speri		
	D26 4,500,563	02/1985	Ellenberger et al.		
	D27 4,508,056	04/1985	Bruel et al.		
	D28 4,536,657	08/1985	Bruel		
	D29 4,539,050	09/1985	Kramler et al.		
	D30 4,542,863	09/1985	Larson		
	D31 4,566,403	01/1986	Fournier		
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	D33 4,568,563	02/1986	Jackson et al.		
	D34 4,585,945	04/1986	Bruel et al.		
	D35 4,630,093	12/1986	Yamaguchi et al.		
	D36 4,684,535	08/1987	Heinecke et al.		
	D37 4,704,302	11/1987	Bruel et al.		
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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

	D38	4,717,683	01/1988	Parrillo et al.		
	D39	4,764,394	08/1988	Conrad		
	D40	4,837,172	06/1989	Mizuno et al.		
	D41	4,846,928	07/1989	Dolins et al.		
	D42	4,847,792	07/1989	Barna et al.		
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	D44	4,887,005	12/1989	Rough et al.		
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	D46	4,894,709	01/1990	Phillips et al.		
	D47	4,904,610	02/1990	Shyr		
	D48	4,920,396	04/1990	Shinohara et al.		
	D49	4,929,566	05/1990	Beitman		
	D50	4,931,405	06/1990	Kamijo et al.		
	D51	4,948,458	08/1990	Ogle		
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	D54	4,960,073	10/1990	Suzuki et al.		
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	D57	4,996,077	02/1991	Moslehi et al.		
	D58	5,013,681	05/1991	Godbey et al.		
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	D60	5,034,343	07/1991	Rouse et al.		
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	D62	5,110,748	05/1992	Sarma		
	D63	5,120,666	06/1992	Gotou		
	D64	5,138,422	08/1992	Fujii et al.		
	D65	5,198,371	03/1993	Li		
	D66	5,200,805	04/1993	Parsons et al.		
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	D69	5,250,446	10/1993	Osawa et al.		
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	D71	5,259,247	11/1993	Bantien		
	D72	5,310,446	05/1994	Konishi et al.		
	D73	5,413,951	05/1995	Ohori et al.		
	D74	5,442,205	08/1995	Brasen et al.		
	D75	5,494,835	02/1996	Bruel		
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	D79	5,611,316	03/1997	Oshima et al.		
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	D80	5,618,739	04/1997	Takahashi et al.		
	D81	5,622,896	04/1997	Knotter et al.		
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	D85	5,741,733	04/1998	Bertagnolli et al.		
	D86	5,753,038	05/1998	Vichr et al.		
	D87	5,804,086	09/1998	Bruel		
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	D89	5,863,830	01/1999	Bruel et al.		
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EXAMINER INITIAL	DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
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	D192 EP 0 383 391 A1	08/1990	EPO		
	D193 EP 0 504 714 A2	09/1992	EPO		
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	D195 EP 0 665 588 A1	08/1995	EPO		ABSTRACT
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	D198 EP 0 849 788 A2	06/1998	EPO		
	D199 EP 0 889 509 A2	01/1999	EPO		
	D200 EP 0 895 282 A2	02/1999	EPO		
	D201 EP 0 898 307 A1	02/1999	EPO		ABSTRACT
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	D203	EP 1 059 663 A2	12/2000	EPO		
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	D205	DE 101 53 319 A1	05/2003	GERMANY		ABSTRACT
	D206	FR 95 08882	06/1996	FRANCE		ABSTRACT
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	D216	JP 53-104156 A	09/1978	JAPAN		ABSTRACT
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	D234	Agarwal, Aditya et al. "Efficient Production of Silicon-On-Insulator Films by Co-Implantation of He ⁺ with H ⁺ " – Proceedings 1997 IEEE International SOI Conference, October 1997 – pp. 44-45.
	D235	Ahn, K. Y., et al., "Growth, Shrinkage, And Stability of Interfacial Oxide Layers Between Directly Bonded Silicon Wafers", <i>Applied Physics A.</i> , Vol. 50, 1990, pp 85-94.

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	D236 Alley et al., "Surface Roughness Modification of Interfacial Contacts In Polysilicon Microstructures", Proceedings of the 7 th International Conference on Solid-State Sensors and Actuators, <i>Transducers '93</i> , PACIFICCO, Yokohama JAPAN. Jun 7-10, 1993, pp 288-291.
	D237 Almedia et al. "Bond formation in ion beam synthesized amorphous gallium nitride", <i>Elsevier, This Solid Films</i> , 343-344 1999, pp 632-636.
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	D246 Aspar et al., Smart-Cut®: The basic fabrication process for UNIBOND® SOI wafers, <i>SEMI</i> 1996, pp. 37-46.
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	D248 Aspar, B. et al, "Characterization of SOI substrates: Application to Recent SIMOX and UNIBOND Wafers," <i>Electrochemical Society Proceedings</i> , vol. 96-3, pp. 99-111, January 1996.
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D365	Stephen, D., "Investigation of Lattice Strain in Proton-Irradiated GaP by a Modified Auleyner Technique" <i>Phys. stat. sol. (a)</i> 87, 1985, pp. 589- 596.
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D367	Sze, S.M., <i>VLSI Technology</i> , 2 ^{sup.nd} Ed., 1988, pp. 9-10.
D368	Tan, T. Y. et al., "On Oxygen Precipitation Retardation/Recovery Phenomena, Nucleation Incubation Phenomena and The Exigent-Accommodation-Volume Factor of Precipitation", Proceedings of the 5 th International Symposium On Silicon Materials Science and Technology, <i>Semiconductor Silicon 198 Electrochem. Soc.</i> , New Jersey, 1986, pp 864-873.

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF11653US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D369	Terada, K. et al., "A New Dram Cell With A Transistor On A Lateral Epitaxial Silicon Layer (Tol Cell)", <i>IEEE Transactions On Electron Device</i> , Vol. 37, No. 9, 1990, pp 2052-2057.
D370	Theodore, N. David et al., "TFSOI With Improved Oxidation Resistance (To Reduce Isolation Induced Stresses and Leakage), Motorola Bulletin XP 000691920, <i>Technical Developments</i> , Nov. 1996, pp 158-59.
D371	Tillman et al., "Zero-Level Packaging for MEMS or MST Devices: The IRS Method", <i>MEMS/Sensors, Advancing Microelectronics</i> , Pages 37-39, November/December 2000.
D372	Tomisaka et al., "Electroplating Cu Fillings for Through-Vias for Three-Dimensional Chip Stacking" (Electronic Components and Technology Conference, 2002).
D373	Tonini, Monelli, Corni, Ottaviani, Frabboni, Canteri, Queirolo, "Hydrogen Interaction with phosphorus ion implanted silicon", <i>Ion Implantation Technology -94</i> , (1995) pp. 801-804.
D374	Tzeng, J.C., "A Novel Self-Aligned Oxygen (Salox) Implanted SOI Mosfet Device Structure" <i>Nuclear Instruments and Methods in Physics Research B2</i> , 1987, pp. 112-115.
D375	U.S. Dept. of Energy, "The Fusion Connection: Contributions to Industry, Defense, and Basic Science Resulting From Scientific Advances Made in the Magnetic Fusion Energy Program", <i>Plasma Coating</i> , pp. 6-7, 1985.
D376	Van de Walle, C. "Structural Identification of Hydrogen and Muonium Centers in Silicon First Principles Calculations of Hyperfine Parameters", <i>Physical Review Letters</i> , Vol. 60, No. 26, 1988, pp 2761-2764.
D377	Van de Walle, C. "Theoretical Aspects of Hydrogen in Crystalline Semiconductors", <i>Physica B</i> , Holland, Vol. 170, No. 15, 1991, pp 21-32.
D378	Van de Walle, C. "Theory of Hydrogen Diffusion and Reactions in Crystalline Silicon", <i>Physical Review Letters</i> , Vol. 64, No. 6, 1980, pp 669-672.
D379	Van de Walle, C. "Theory of Hydrogen Diffusion and Reactions in Crystalline Silicon", <i>Physical Review B</i> , Vol. 39, No. 15, 1989, pp 10 791-10 808, plus diagrams.
D380	Van Swijgenhoven et al. "Helium Bubble and Blister Formation for Nickel and An AMorphous Fe-Ni-Mo-B Alloy During 5 kev He ⁺ -Irradiation at Temperatures Between 200 K and 600", <i>Nuclear Instruments and Methods</i> , 209/210, 1983, pp. 461-468.
D381	Veldkamp, W.B. et al., "Binary Optics," <i>Scientific American</i> , 1992, pp. 50-55.
D382	Venezia et al., "The Role of Implantation Damage in the Production of Silicon-On-Insulator Films By Co-Implantation Of He ⁺ and H ⁺ ", <i>Electrochemical Society Proceedings Volume 98-1</i> , 1998 - pp. 1384-1395.
D383	Weldon et al., "Mechanism Of Silicon Exfoliation Induced by Hydrogen/Helium Co-implantation", <i>Applied Physics Letters</i> , Vol, 73, No. 25, pp 3721-3723, Dec 21, 1998.

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	D384	Wemple, S.H., "Optical and channeling studies of ion-bombarded GaP", <i>J. Appl. Phys.</i> , vol. 45, No.4, Apr. 1974, pp 1578-1588.
	D385	Whitton, J. L. et al., "The Collection of Ions Implanted In Semiconductors: 1 Saturations Effects", <i>Radiation Effects</i> , Scotland, Vol. 16, 1972, pp 101-105.
	D386	Wiegand, M. et al., "Wafer Bonding of Silicon Wafers Covered With Various Surface Layers", <i>Sensors and Actuators</i> , Elsevier Science B.V., Vol. 86, 2000, pp 91-95.
	D387	Williams J. et al., "Annealing behaviour of high-dose rare-gas implantations into silicon", from Application of Ion Beams to Materials, 1975, Chap. 1, <i>Inst. Phys. Conf. Ser. No. 28</i> , 1976, pp 30-36.
	D388	Wittmaack et al., "High Fluence Retention of Noble Gases Implanted in Silicon" <i>Radiation Effects</i> , vol. 39, 1978, pp. 81-95.
	D389	Wolf, Stanley Ph.D., Silicon Processing for the VLSI Era (vol. 2), Lattice Press, 1990, pp. 66-79.
	D390	Yamaguchi H. et al., "Intelligent Power IC With Partial Soi Structure", <i>Jpn. J. Appl. Phys.</i> , Vol. 34, 1995, pp 864-868.
	D391	Yee et al., "Polysilicon Surface-Modification Technique to Reduce Sticking of Microstructures", <i>Sensors and Actuators A</i> 52, 1996, pp. 145-150.
	D392	Yun, H. et al., "Transfer of Patterned A-Cut Silicon Layers", <i>Applied Physics Letters</i> , Vol. 73, No. 19, 1998, pp 2772-2774.
	D393	International Search Report for International Application No. PCT/FR1998/002904, dated April 16, 1999, 2 pages.
	D394	International Search Report for International Application No. PCT/FR2002/003422, dated January 22, 2003, 3 pages.
	D395	International Search Report for International Application No. PCT/FR2003/003256, dated March 19, 2004, 6 pages.
	D396	International Search Report for International Application No. PCT/FR2003/003867, dated May 28, 2004, 3 pages.
	D397	International Search Report for International Application No. PCT/FR2003/003622, dated June 3, 2004, 3 pages.
	D398	International Search Report for International Application No. PCT/FR2004/001858, dated December 28, 2004, 3 pages.
	D399	International Search Report for International Application No. PCT/FR2004/002779, dated April 5, 2005, 3 pages.
	D400	International Search Report for International Application No. PCT/FR2004/002781, dated April 5, 2005, 3 pages.
	D401	International Search Report for International Application No. PCT/FR2004/001565, dated July 6, 2005, 3 pages.
	D402	International Search Report for International Application No. PCT/FR2006/002184, dated January 24, 2007, 2 pages.

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	D403	International Search Report for International Application No. PCT/FR2007/000534, dated November 22, 2007, 3 pages.
	D404	International Search Report for International Application No. PCT/FR2007/002100, dated February 4, 2009, 3 pages.
	D405	International Search Report for International Application No. PCT/FR2008/001427, dated July 1, 2009, 3 pages.
	D406	Office Action from US Application No. 12/063,808, dated April 6, 2010, 9 pages.
	D407	Office Action from US Application No. 12/063,808, dated September 22, 2010, 9 pages.
	D408	Office Action from US Application No. 10/534,199, dated February 19, 2009, 8 pages.
	D409	Office Action from US Application No. 10/534,199, dated August 5, 2009, 10 pages.
	D410	Office Action from US Application No. 10/534,199, dated January 20, 2010, 8 pages.
	D411	Office Action from US Application No. 10/534,199, dated August 4, 2010, 8 pages.
	D412	Office Action from US Application No. 11/480,250, dated May 22, 2008, 10 pages.
	D413	Office Action from US Application No. 11/480,250, dated December 3, 2008, 16 pages.
	D414	Office Action from US Application No. 11/480,250, dated January 26, 2010, 14 pages.
	D415	Office Action from US Application No. 11/480,250, dated August 3, 2010, 15 pages.
	D416	Office Action from US Application No. 12/088,047, dated September 25, 2009, 9 pages.
	D417	Office Action from US Application No. 12/088,047, dated March 10, 2010, 9 pages.
	D418	Office Action from US Application No. 10/561,299, dated March 26, 2008, 9 pages.
	D419	Office Action from US Application No. 10/561,299, dated December 9, 2008, 11 pages.
	D420	Office Action from US Application No. 10/561,299, dated May 11, 2009, 12 pages.
	D421	Office Action from US Application No. 10/561,299, dated November 16, 2009, 11 pages.
	D422	Office Action from US Application No. 10/561,299, dated November 27, 2009, 10 pages.
	D423	Office Action from US Application No. 10/561,299, dated May 11, 2010, 11 pages.
	D424	Office Action from US Application No. 10/565,621, dated May 15, 2007, 13 pages.
	D425	Office Action from US Application No. 10/565,621, dated February 11, 2008, 11 pages.
	D426	Office Action from US Application No. 10/565,621, dated September 12, 2008, 9 pages.
	D427	Office Action from US Application No. 10/565,621, dated March 12, 2009, 6 pages.
	D428	Office Action from US Application No. 10/565,621, dated January 7, 2010, 8 pages.
	D429	Office Action from US Application No. 10/565,621, dated November 23, 2010, 11 pages.
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	D430 Office Action from US Application No. 12/628,772, dated October 7, 2010, 12 pages.
	D431 Notice of Allowance from US Application No. 12/336,229, dated September 29, 2010, 7 pages.
	D432 Notice of Allowance from US Application No. 12/336,229, dated January 10, 2011, 4 pages.
	D433 Office Action from US Application No. 10/468,223, dated October 5, 2005, 7 pages.
	D434 Office Action from US Application No. 10/468,223, dated May 3, 2006, 11 pages.
	D435 Office Action from US Application No. 10/468,223, dated January 10, 2007, 11 pages.
	D436 Office Action from US Application No. 10/468,223, dated July 20, 2007, 11 pages.
	D437 Office Action from US Application No. 10/468,223, dated February 11, 2008, 11 pages.
	D438 Office Action from US Application No. 10/468,223, dated October 29, 2008, 11 pages.
	D439 Office Action from US Application No. 10/468,223, dated June 25, 2009, 8 pages.
	D440 Notice of Allowance from US Application No. 10/468,223, dated December 28, 2009, 4 pages.
	D441 Office Action from US Application No. 10/474,984, dated September 24, 2004, 6 pages.
	D442 Office Action from US Application No. 10/474,984, dated June 6, 2005, 5 pages.
	D443 Office Action from US Application No. 10/474,984, dated November 16, 2005, 5 pages.
	D444 Office Action from US Application No. 10/474,984, dated May 17, 2006, 5 pages.
	D445 Office Action from US Application No. 10/474,984, dated May 7, 2007, 9 pages.
	D446 Office Action from US Application No. 10/474,984, dated February 6, 2008, 10 pages.
	D447 Office Action from US Application No. 10/474,984, dated October 17, 2008, 11 pages.
	D448 Office Action from US Application No. 10/474,984, dated July 7, 2009, 10 pages.
	D449 Office Action from US Application No. 10/474,984, dated March 11, 2010, 13 pages.
	D450 Notice of Allowance from US Application No. 10/474,984, dated October 28, 2010, 6 pages.
	D451 Office Action from US Application No. 10/540,303, dated December 18, 2007, 6 pages.
	D452 Notice of Allowance from US Application No. 10/540,303, dated October 7, 2008, 9 pages.
	D453 Office Action from US Application No. 11/327,906, dated October 1, 2007, 5 pages.
	D454 Office Action from US Application No. 11/327,906, dated February 11, 2008, 5 pages.
	D455 Notice of Allowance from US Application No. 11/327,906, dated September 15, 2008, 6 pages.
	D456 Office Action from US Application No. 10/975,826, dated September 2, 2009, 24 pages.

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D457	Notice of Allowance from US Application No. 10/975,826, dated April 28, 2010, 8 pages.
D458	Office Action from US Application No. 10/492,343, dated October 17, 2005, 6 pages.
D459	Office Action from US Application No. 10/492,343, dated June 6, 2006, 13 pages.
D460	Office Action from US Application No. 10/492,343, dated November 14, 2006, 13 pages.
D461	Office Action from US Application No. 10/492,343, dated May 29, 2007, 15 pages.
D462	Office Action from US Application No. 10/492,343, dated February 7, 2008, 18 pages.
D463	Office Action from US Application No. 10/492,343, dated August 18, 2008, 12 pages.
D464	Office Action from US Application No. 10/492,343, dated December 22, 2008, 9 pages.
D465	Notice of Allowance from US Application No. 10/492,343, dated June 26, 2009, 6 pages.
D466	Office Action from US Application No. 11/747,733, dated March 16, 2009, 9 pages.
D467	Office Action from US Application No. 11/747,733, dated March 23, 2010, 5 pages.
D468	Notice of Allowance from US Application No. 11/747,733, dated September 29, 2010, 8 pages.
D469	Notice of Allowance from US Application No. 12/293,193, dated October 8, 2009, 10 pages.
D470	Expert Report of Marcus Weldon, Ph.D. dated November 1, 2000
D471	Expert Report of Jean-Pierre Colinge dated November 1, 2000.
D472	Expert Report of Chris Van de Walle, Ph.D. dated November 1, 2000
D473	Memorandum in Support of Defendant Silicon Genesis Corporation's Motion for Summary Judgment of Invalidity for Lack of Enablement dated March 19, 2001
D474	Memorandum of Points and Authorities In Support of Soitec's Motion for Summary Judgment on SiGen's Enablement Invalidity Claim (Redacted) dated March 27, 2001
D475	Soitec's Memorandum of Points and Authorities In Opposition to Silicon Genesis Corporation's Motion for Summary Judgment of Invalidity for Lack of Enablement dated April 11, 2001
D476	Memorandum in Support of Defendant Silicon Genesis Corporation's Opposition to Soitec's Motion for Summary Judgment on SiGen's Defense of Enablement dated April 20, 2001
D477	Reply Memorandum in Support of Defendant Silicon Genesis Corporation's Motion for Summary Judgment of Invalidity for Lack of Enablement dated April 30, 2001
D478	Expert Report of Marcus Weldon, Ph.D. dated August 24, 2001
D479	Report of Jean-Pierre Colinge in Response to SiGen Enablement and Indefiniteness Expert Reports of August 24, 2001

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D480	Expert Report of Chris Van de Walle, Ph.D. dated August 24, 2001
D481	Memorandum and Order re: Summary Judgment [denied] dated February 5, 2002
D482	Plaintiff's Memorandum in Support of Their Motion for Judgment As a Matter of Law and a New Trial dated May 10, 2002
D483	Silicon Genesis Corporation's Opposition to Plaintiff's Motion for Judgment as a Matter of Law and a New Trial dated June 17, 2002
D484	Memorandum of Law in Support of Plaintiff's Motion for Judgment on SiGen's Indefiniteness Defense dated June 20, 2002
D485	Plaintiff's Reply Memorandum in Support of Their Motion for Judgment as a Matter of Law and a New Trial dated July 18, 2002
D486	Defendant Silicon Genesis Corporation's Opposition to Soitec's Motion for Judgment Re Indefiniteness and Cross-Motion for Judgment of Indefiniteness dated July 19, 2002
D487	Plaintiff's Reply in Support of their Motion for Judgment on SiGen's Indefiniteness Defense dated July 25, 2002
D488	Memorandum and Order re: Post-Trial Motions dated August 23, 2002
D489	Judgment dated October 21, 2002.
D490	Brief of Plaintiffs-Appellants Soitec, S.A. and Commissariat a L'Energie Atomique dated January 28, 2003
D491	Brief for Defendant-Cross Appellant Silicon Genesis Corporation dated March 22, 2003
D492	Reply Brief of Plaintiffs-Appellants Soitec, S.A. and Commissariat a L'Energie Atomique dated May 5, 2003
D493	Reply Brief for Defendant-Cross Appellant Silicon Genesis Corporation dated May 19, 2003
D494	Plaintiff/Appellants Supplemental Authority Letter [dated November 17, 2003].
D495	Defendant-Cross Appellant's Response To Appellants' Submission Of <i>CFMT, Inc. v. Yieldup Int'l</i> , [dated November 24, 2003].
D496	Decision from the United States Court of Appeals for the Federal Circuit dated November 26, 2003.
D497	Combined Petition for Panel Rehearing and for Rehearing En Banc by Plaintiffs-Appellant's Soitec, S.A. and Commissariat A L'Energie Atomique, dated December 10, 2003.
D498	Order [dated January 7, 2004 denying Appellants' petition for panel rehearing and Appellant's petition for rehearing en banc].
D499	Judgment Mandate [dated January 14, 2004].

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D500	NOTICE of by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique re <u>30</u> MOTION to Dismiss Based upon Fed. R. Civ. P. 12(b)(1) and (6) and Article III of the United States Constitution MOTION to Dismiss Based upon Fed. R. Civ. P. 12(b)(1) and (6) and Article III of the United States Constitution Notice of Withdrawal of Plaintiffs' Partial Motion to Dismiss Counterclaim Counts II, III, IV, V, and VIII (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2009)
D501	STIPULATION and [Proposed] Order to File an Amended Complaint by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/16/2009)
D502	NOTICE OF SERVICE of Soitec's Objections and Responses to MEMC's Second Request For Production of Documents and Things Directed To Soitec re <u>46</u> Notice of Service by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. Related document: <u>46</u> Notice of Service filed by MEMC Electronic Materials Inc. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/16/2009)
D503	First AMENDED COMPLAINT for Patent Infringement against MEMC Electronic Materials Inc.- filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Exhibit Exhibit 1, # <u>2</u> Exhibit Exhibit 2, # <u>3</u> Exhibit Exhibit 3, # <u>4</u> Exhibit Exhibit 4, # <u>5</u> Certificate of Service)(Kraft, Denise) (Entered: 07/21/2009)
D504	ANSWER to Amended Complaint ANSWER to <u>57</u> Amended Complaint, with Under Federal Rule of Civil Procedure 38, MEMC demands a trial by jury on all issues so triable., COUNTERCLAIM against all plaintiffs by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2009)
D505	ANSWER to <u>60</u> Answer to Amended Complaint, Counterclaim,,, COUNTERCLAIM Reply to Defendant's Amended Counterclaims, Counterclaims And Affirmative Defenses against MEMC Electronic Materials Inc. by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/31/2009)
D506	NOTICE OF SERVICE of MEMC's THIRD SET OF INTERROGATORIES DIRECTED TO S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES, S.A., SOITEC USA, INC., AND COMMISSARIAT A L'ENERGIE ATOMIQUE by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 09/01/2009)

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D507	ANSWER to <u>68</u> Answer to Counterclaim,,, by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 09/14/2009). Minute Entry for proceedings held before Judge Sue L. Robinson - Discovery Conference held on 9/16/2009. (Court Reporter V. Gunning.) (nmf) (Entered: 09/16/2009)
D508	MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order - filed by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 10/20/2009). CORRECTING ENTRY: Docket clerk deleted D.I. 78 (opening brief) due to document being filed improperly. Counsel is advised to re-file document using the OPENING BRIEF event code rather than the combined opening and answering brief event code. (lid) (Entered: 10/21/2009)
D509	OPENING BRIEF in Support re <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order filed by MEMC Electronic Materials Inc..Answering Brief/Response due date per Local Rules is 11/9/2009. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C)(Rogowski, Patricia) (Entered: 10/21/2009)
D510	Cross MOTION to Bifurcate all Collateral Issues - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a LEnergie Atomique. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/09/2009)
D511	ANSWERING BRIEF in Opposition re <u>85</u> Cross MOTION to Bifurcate all Collateral Issues, <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a LEnergie Atomique.Reply Brief due date per Local Rules is 11/20/2009. (Attachments: # <u>1</u> Exhibit, # <u>2</u> Exhibit, # <u>3</u> Exhibit, # <u>4</u> Exhibit, # <u>5</u> Exhibit, # <u>6</u> Exhibit, # <u>7</u> Exhibit, # <u>8</u> Exhibit, # <u>9</u> Exhibit, # <u>10</u> Exhibit, # <u>11</u> Exhibit, # <u>12</u> Declaration, # <u>13</u> Certificate of Service)(Kraft, Denise) (Entered: 11/09/2009)
D512	REPLY BRIEF re <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3)(Rogowski, Patricia) (Entered: 11/17/2009)
D513	ANSWERING BRIEF in Opposition re <u>85</u> Cross MOTION to Bifurcate all Collateral Issues filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 12/3/2009. (Rogowski, Patricia) (Entered: 11/19/2009)

EXAMINER	DATE CONSIDERED
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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D514	REPLY BRIEF re <u>85</u> Cross MOTION to Bifurcate all Collateral Issues filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit Declaration of Marcus T. Hall in Support of Plaintiffs Reply Re: Cross-Motion to Bifurcate all Collateral Issues)(Kraft, Denise) (Entered: 12/03/2009)
D515	NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Production of Three Boxes of Wafer Samples by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 12/08/2009). Set Hearings: Discovery Conference set for 12/21/2009 04:00 PM in Courtroom 6B before Judge Sue L. Robinson. (nmf) (Entered: 12/09/2009).
D516	MOTION for Leave to File Stipulated Motion for Leave to File a Sur-Reply Brief in Support of MEMC's Motion to Bifurcate - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1)(Rogowski, Patricia) (Entered: 12/14/2009)
D517	SUR-REPLY BRIEF re <u>ZZ</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order MEMC's SUR-REPLY BRIEF IN SUPPORT OF ITS MOTION TO BIFURCATE THE ISSUES OF WILLFULNESS AND DAMAGES FOR PURPOSES OF DISCOVERY AND TRIAL filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/16/2009)
D518	MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 05/07/2010)
D519	OPENING BRIEF in Support re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 filed by MEMC Electronic Materials Inc.. Answering Brief/Response due date per Local Rules is 5/24/2010. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3, # <u>4</u> Exhibit 4, # <u>5</u> Exhibit 5, # <u>6</u> Exhibit 6, # <u>7</u> Exhibit 7, # <u>8</u> Exhibit 8, # <u>9</u> Exhibit 9, # <u>10</u> Exhibit 10, # <u>11</u> Exhibit 11, # <u>12</u> Exhibit 12, # <u>13</u> Exhibit 13, # <u>14</u> Exhibit 14, # <u>15</u> Exhibit 15)(Rogowski, Patricia) (Entered: 05/07/2010)

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(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

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D520	ANSWERING BRIEF in Opposition re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 Plaintiff's Answering Brief in Opposition to Defendant's Motion For the Admission of Expert Testimony of John T. Goolkasian filed by SOITEC Silicon On Insulator Technologies SA. Reply Brief due date per Local Rules is 6/4/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 05/24/2010)
D521	DECLARATION re <u>145</u> Answering Brief in Opposition,, Declaration of Marcus T. Hall in Support of Plaintiffs Answering Brief in Opposition to Defendant's Motion For the Admission of Expert Testimony of John T. Goolkasian by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Exhibit E, # <u>6</u> Exhibit F, # <u>7</u> Exhibit G, # <u>8</u> Exhibit H, # <u>9</u> Exhibit I, # <u>10</u> Exhibit J, # <u>11</u> Exhibit K, # <u>12</u> Exhibit L, # <u>13</u> Exhibit M, # <u>14</u> Exhibit N, # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 05/24/2010)
D522	REPLY BRIEF IN SUPPORT OF <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3, # <u>4</u> Exhibit 4, # <u>5</u> Exhibit 5, # <u>6</u> Exhibit 6)(Rogowski, Patricia) Modified on 6/4/2010 (ltd). (Entered: 06/04/2010)
D523	STATEMENT re <u>148</u> Stipulation Joint Claim Construction Statement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/14/2010)
D524	CLAIM Construction Chart by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/14/2010)
D525	SUR-REPLY BRIEF re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 Surreply by Plaintiffs to Motion by Defendant For The Admission of Expert Testimony of John T. Goolkasian filed by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/15/2010)
D526	DECLARATION re <u>157</u> Sur-Reply Brief, Declaration of Marcus T. Hall in Support of Surreply by Plaintiffs to Motion by Defendant For The Admission of Expert Testimony of John T. Goolkasian by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Certificate of Service)(Kraft, Denise) (Entered: 06/15/2010)
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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
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(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

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D527	CLAIM CONSTRUCTION OPENING BRIEF filed by MEMC Electronic Materials Inc.. (Attachments: # 1 Appendix DA0001-DA0006, # 2 Appendix DA0007-DA0032, # 3 Appendix DA0033-DA0072, # 4 Appendix DA0073-DA0112, # 5 Appendix DA0113-DA0152, # 6 Appendix DA0153-DA0192, # 7 Appendix DA0193-DA0232, # 8 Appendix DA0233-DA0272, # 9 Appendix DA0273-DA0312, # 10 Appendix DA0313-DA0352, # 11 Appendix DA0353-DA0392, # 12 Appendix DA0393-DA0432, # 13 Appendix DA0433-DA0472, # 14 Appendix DA0473-DA0512, # 15 Appendix DA0513-DA0521, # 16 Appendix DA0522-DA0545, # 17 Appendix SEALED - DA0546-DA0551, # 18 Appendix DA0552-DA0563, # 19 Appendix SEALED - DA0564-DA0566, # 20 Appendix DA0567-DA0573, # 21 Appendix SEALED - DA0574-DA0599, # 22 Appendix DA0600-DA0604, # 23 Appendix DA0605-DA0609, # 24 Appendix DA0610-DA0625, # 25 Appendix DA0626-0634, # 26 Appendix DA0635, # 27 Appendix DA0636-DA0652, # 28 Appendix SEALED - DA0653-DA0657, # 29 Appendix DA0658-DA0667, # 30 Appendix DA0668-DA0670, # 31 Appendix DA0671-DA0678, # 32 Appendix DA0679-DA0687, # 33 Appendix DA0688-DA0696, # 34 Appendix SEALED - DA0697-DA0705, # 35 Appendix SEALED - DA0706-DA0711, # 36 Appendix SEALED - DA0712-DA0714, # 37 Appendix DA0715-DA0717, # 38 Appendix DA0718-DA0719, # 39 Appendix DA0720-DA0722, # 40 Appendix DA0723-DA0732, # 41 Appendix DA0733-DA0740, # 42 Appendix DA0741-DA0749, # 43 Appendix DA0750-DA0769, # 44 Appendix DA0770-DA0781)(Rogowski, Patricia) (Entered: 06/25/2010)
D528	CLAIM CONSTRUCTION OPENING BRIEF Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)
D529	DECLARATION re <u>168</u> Claim Construction Opening Brief, Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF11653US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D530	APPENDIX re <u>167</u> Claim Construction Opening Brief,,,,, by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix DA-0001 - DA-0006, # <u>2</u> Appendix DA-0007 - DA-0032, # <u>3</u> Appendix DA-0033 - DA-0072, # <u>4</u> Appendix DA-0073 - DA-0112, # <u>5</u> Appendix DA-0113 - DA-0152, # <u>6</u> Appendix DA-0153 - DA-0192, # <u>7</u> Appendix DA-0193 - DA-0232, # <u>8</u> Appendix DA-0233 - DA-0272, # <u>9</u> Appendix DA-0273 - DA-0312, # <u>10</u> Appendix DA-0313 - DA-0352, # <u>11</u> Appendix DA-0353 - DA-0392, # <u>12</u> Appendix DA-0393 - DA-0432, # <u>13</u> Appendix DA-0433 - DA-0472, # <u>14</u> Appendix DA-0473 - DA-0512, # <u>15</u> Appendix DA-0513 - DA-0521)(Rogowski, Patricia) (Entered: 06/28/2010)
D531	REDACTED VERSION of <u>175</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix DA0522-DA0545, # <u>2</u> Appendix DA0546-DA0551, # <u>3</u> Appendix DA0552-DA0563, # <u>4</u> Appendix DA0564-DA0566, # <u>5</u> Appendix DA0567-DA0573, # <u>6</u> Appendix DA0574-DA0599, # <u>7</u> Appendix DA0600-DA0604, # <u>8</u> Appendix DA0605-DA0609, # <u>9</u> Appendix DA0610-DA0625, # <u>10</u> Appendix DA0626-DA0634, # <u>11</u> Appendix DA0635, # <u>12</u> Appendix DA0636-DA0652, # <u>13</u> Appendix DA0653-DA0657, # <u>14</u> Appendix DA0658-DA0667, # <u>15</u> Appendix DA0668-DA0670, # <u>16</u> Appendix DA0671-DA0678, # <u>17</u> Appendix DA0679-DA0687, # <u>18</u> Appendix DA0688-DA0696, # <u>19</u> Appendix DA0697-DA0705, # <u>20</u> Appendix DA0706-DA0711, # <u>21</u> Appendix DA0712-DA0714, # <u>22</u> Appendix DA0715-DA0717, # <u>23</u> Appendix DA0718-DA0719, # <u>24</u> Appendix DA0720-DA0722, # <u>25</u> Appendix DA0723-DA0732, # <u>26</u> Appendix DA0733-DA0740, # <u>27</u> Appendix DA0741-DA0749, # <u>28</u> Appendix DA0750-DA0769, # <u>29</u> Appendix DA0770-DA0781, # <u>30</u> Certificate of Service)(Rogowski, Patricia) (Entered: 06/28/2010)
D532	NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (1) Vol. I - JA0001 to JA0533. APPENDIX VOL I. re <u>173</u> Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE). (lid) (Entered: 06/28/2010).
D533	NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (2) Vol. II - JA0534 to JA0930. APPENDIX VOL II. re <u>173</u> Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE). (lid) (Entered: 06/28/2010).
D534	NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (3) Vol. III - JA0931 to JA1502. APPENDIX VOL III. re <u>173</u> Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE) (lid) (Entered: 06/28/2010) (2 parts).

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D535	NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (4) Vol. IV – JA1503 to JA1510. APPENDIX VOL IV. re 173 Notice of Filing Paper Documents, (OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE) (lid) (Entered: 06/28/2010).
D536	NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (5) Vol. V – JA1511 to JA2089 (2 parts).
D537	Vol. VI - JA2090 to JA2557. Original document(s) to be filed with the Clerk's Office. Notice filed by Denise Seastone Kraft on behalf of Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010).
D538	MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Text of Proposed Order, # 2 Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D539	MOTION for Partial Summary Judgment of Invalidity of the Asserted Aspar Patent Claims - filed by MEMC Electronic Materials Inc.. (Attachments: # 1 Text of Proposed Order, # 2 Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)
D540	OPENING BRIEF in Support re 186 MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # 1 Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D541	OPENING BRIEF in Support re 187 MOTION for Partial Summary Judgment of Invalidity of the Asserted Aspar Patent Claims filed by MEMC Electronic Materials Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Rogowski, Patricia) (Entered: 07/02/2010)

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D542	APPENDIX re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony Plaintiffs' Omnibus Appendix to Daubert Motion and Motions For Partial Summary Judgment Filed on July 2, 2010 by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Appendix Vol. II of XIX, # <u>2</u> Appendix Vol. III of XIX, # <u>3</u> Appendix Vol. IV of XIX, # <u>4</u> Appendix Vol. V of XIX, # <u>5</u> Appendix Vol. VII of XIX, # <u>6</u> Appendix Vol. IX of XIX, # <u>7</u> Appendix Vol. XI of XIX, # <u>8</u> Appendix Vol. XII of XIX, # <u>9</u> Appendix Vol. XIII of XIX, # <u>10</u> Appendix Vol. XIV of XIX, # <u>11</u> Appendix Vol. XV of XIX, # <u>12</u> Appendix Vol. XVI of XIX, # <u>13</u> Appendix Vol. XVIII of XIX, # <u>14</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D543	MOTION for Summary Judgment of Non-Infringement - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)
D544	MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D545	OPENING BRIEF in Support re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D546	MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D547	OPENING BRIEF in Support re <u>204</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)

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D548	MOTION for Partial Summary Judgment SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D549	OPENING BRIEF in Support re <u>206</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D550	MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D551	OPENING BRIEF in Support re <u>208</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D552	MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D553	OPENING BRIEF in Support re <u>210</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D554	MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D555	MOTION for Partial Summary Judgment That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents - filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Reed, John) (Entered: 07/02/2010)
D556	OPENING BRIEF in Support re <u>212</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
D557	OPENING BRIEF in Support re <u>213</u> MOTION for Partial Summary Judgment That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents filed by SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Reed, John) (Entered: 07/02/2010)
D558	REDACTED VERSION of <u>200</u> Opening Brief in Support, by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/07/2010)

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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)
D559	REDACTED VERSION of <u>201</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0001 - MA0004, # <u>2</u> Appendix MA0005 - MA0010, # <u>3</u> Appendix MA0011 - MA0016, # <u>4</u> Appendix MA0017 - MA0020, # <u>5</u> Appendix MA0021 - MA0029, # <u>6</u> Appendix MA0030 - MA0045, # <u>7</u> Appendix MA0046 - MA0052, # <u>8</u> Appendix MA0053 - MA0078, # <u>9</u> Appendix MA0079 - MA0092, # <u>10</u> Appendix MA0093 - MA0129, # <u>11</u> Appendix MA0130 - MA0148, # <u>12</u> Appendix MA0149 - MA0160, # <u>13</u> Appendix MA0161 - MA0163, # <u>14</u> Appendix MA0164 - MA0167, # <u>15</u> Appendix MA0168 - MA0172, # <u>16</u> Appendix MA0173 - MA0183, # <u>17</u> Appendix MA0184 - MA0196, # <u>18</u> Appendix MA0197 - MA0207, # <u>19</u> Appendix MA0208 - MA0241, # <u>20</u> Appendix MA0242 - MA0245, # <u>21</u> Appendix MA0246 - MA0249, # <u>22</u> Appendix MA0250 - MA0252, # <u>23</u> Appendix MA0253 - MA0265, # <u>24</u> Appendix MA0266 - MA0281, # <u>25</u> Appendix MA0282 - MA0312, # <u>26</u> Appendix MA0313 - MA0359, # <u>27</u> Appendix MA0360 - MA0365, # <u>28</u> Appendix MA0366, # <u>29</u> Appendix MA0367 - MA0400, # <u>30</u> Appendix MA0401 - MA0474, # <u>31</u> Appendix MA0475 - MA0483, # <u>32</u> Certificate)(Rogowski, Patricia) (Entered: 07/07/2010)
D560	REDACTED VERSION of <u>190</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0484 - MA0489, # <u>2</u> Appendix MA0490 - MA0515, # <u>3</u> Appendix MA0516 - MA0534, # <u>4</u> Appendix MA0535 - MA0541, # <u>5</u> Appendix MA0542 - MA0550, # <u>6</u> Appendix MA0551 - MA0561, # <u>7</u> Appendix MA0562 - MA0564, # <u>8</u> Appendix MA0565 - MA0569, # <u>9</u> Appendix MA0570 - MA0574, # <u>10</u> Appendix MA0575 - MA0576, # <u>11</u> Appendix MA0577 - MA0601, # <u>12</u> Appendix MA0602 - MA0603, # <u>13</u> Appendix MA0604 - MA0605, # <u>14</u> Appendix MA0606 - MA0609, # <u>15</u> Appendix MA0610 - MA0612, # <u>16</u> Appendix MA0613 - MA0625, # <u>17</u> Appendix MA0626 - MA0628, # <u>18</u> Appendix MA0629 - MA0630, # <u>19</u> Appendix MA0631 - MA0653, # <u>20</u> Appendix MA0654 - MA0685, # <u>21</u> Appendix MA0686 - MA0701, # <u>22</u> Appendix MA0702 - MA0732, # <u>23</u> Appendix MA0733 - MA0742, # <u>24</u> Appendix MA0743 - MA0750, # <u>25</u> Appendix MA0751 - MA0766, # <u>26</u> Appendix MA0767 - MA0772, # <u>27</u> Appendix MA0773 - MA0780, # <u>28</u> Appendix MA0781 - MA0807, # <u>29</u> Appendix MA0808 - MA0824, # <u>30</u> Appendix MA0825 - MA0831.1, # <u>31</u> Appendix MA0832 - MA0838, # <u>32</u> Appendix MA0839 - MA0844, # <u>33</u> Appendix MA0845 - MA0858, # <u>34</u> Appendix MA0859 - MA0868, # <u>35</u> Appendix MA0869 - MA0877, # <u>36</u> Appendix MA0878 - MA0884, # <u>37</u> Appendix MA0885 - MA0887, # <u>38</u> Appendix MA0888 - MA0891, # <u>39</u> Appendix MA0892 - MA0909, # <u>40</u> Appendix MA0910 - MA0931, # <u>41</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/07/2010)
D561	REDACTED VERSION of <u>198</u> Opening Brief in Support,, SOITEC/CEA Parties' Opening Brief In Support Of Motion For Summary Judgment: Non-Infringement by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/08/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D562	REDACTED VERSION of <u>197</u> SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL)SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL) SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/08/2010)
D563	REDACTED VERSION of <u>192</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume VI of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
D564	REDACTED VERSION of <u>193</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume VIII of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
D565	REDACTED VERSION of <u>194</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume X of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
D566	REDACTED VERSION of <u>195</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume XVII of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
D567	REDACTED VERSION of <u>196</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume XIX of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)
D568	CLAIM CONSTRUCTION ANSWERING BRIEF re <u>168</u> Claim Construction Opening Brief, filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/09/2010)
D569	APPENDIX re <u>228</u> Claim Construction Answering Brief by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix DA0782_ DA0783, # <u>2</u> Appendix DA0784 - DA0785, # <u>3</u> Appendix DA0786, # <u>4</u> Appendix DA0787 - DA0810, # <u>5</u> Appendix DA0811 - DA0834, # <u>6</u> Appendix DA0835 - DA0845, # <u>7</u> Appendix DA0846 - DA0855, # <u>8</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/09/2010)

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(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D570	CLAIM CONSTRUCTION ANSWERING BRIEF re <u>168</u> Claim Construction Opening Brief, <u>228</u> Claim Construction Answering Brief Plaintiffs S.O.I.TEC On Insulator Technologies, S.A. And Commissariat A Energie Atomique's Answering Claim Construction Brief filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/09/2010)
D571	APPENDIX re <u>230</u> Claim Construction Answering Brief, Appendix to Plaintiffs S.O.I.TEC On Insulator Technologies, S.A. And Commissariat A Energie Atomique's Answering Claim Construction Brief by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Appendix PA-0001 - PA-0050, # <u>2</u> Appendix PA-0051 - PA-0083, # <u>3</u> Certificate of Service)(Kraft, Denise) (Entered: 07/09/2010)
D572	REDACTED VERSION of <u>183</u> Appendix, Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs Volume IV of VI by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
D573	REDACTED VERSION of <u>170</u> Exhibit to a Document, Exhibit A to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
D574	REDACTED VERSION of <u>171</u> Exhibit to a Document, Exhibit B to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
D575	REDACTED VERSION of <u>172</u> Exhibit to a Document, Exhibit C to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
D576	ANSWERING BRIEF in Opposition re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D577	ANSWERING BRIEF in Opposition re <u>208</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
D578	ANSWERING BRIEF in Opposition re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
D579	ANSWERING BRIEF in Opposition re <u>204</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
D580	ANSWERING BRIEF in Opposition re <u>210</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
D581	ANSWERING BRIEF in Opposition re <u>212</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
D582	APPENDIX re <u>247</u> Answering Brief in Opposition,, Appendix To Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of Invalidity Of The Asserted Aspar Claims (PA-1103 - PA-1156) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Exhibit PA-1103 - PA-1109 - FILED UNDER SEAL, # 2 Exhibit PA-1110 - PA-1118 - FILED UNDER SEAL, # 3 Exhibit PA-1119 - PA-1130 - FILED UNDER SEAL, # 4 Exhibit PA-1131 - PA-1143 - FILED UNDER SEAL, # 5 Exhibit PA-1144 - PA-1156, # 6 Certificate of Service)(Kraft, Denise) (Entered: 07/19/2010)
D583	APPENDIX re <u>250</u> Answering Brief in Opposition, Appendix to Plaintiffs' Answering Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # 1 Exhibit PA-1190 - PA-1191, # 2 Certificate of Service)(Kraft, Denise) (Entered: 07/19/2010)

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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D584	REDACTED VERSION of <u>241</u> Answering Brief in Opposition, to Plaintiffs' Motion for Partial Summary Judgment that the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
D585	REDACTED VERSION of <u>249</u> Answering Brief in Opposition, to Plaintiffs' Motion for Summary Judgment on the Infringement of U.S. Patent No. 5,834,812 by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
D586	REDACTED VERSION of <u>253</u> Answering Brief in Opposition, to Plaintiffs' Motion for Partial Summary Judgment that the Aspar Patents Are Not Invalid for Inequitable Conduct by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
D587	REDACTED VERSION of <u>240</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0932 - MA0985, # <u>2</u> Appendix MA0986 - MA1039.22, # <u>3</u> Appendix MA1040 - MA1144, # <u>4</u> Appendix MA1145 - MA1200, # <u>5</u> Appendix MA1201 - MA1265, # <u>6</u> Appendix MA1265.1 - MA1338, # <u>7</u> Appendix MA1339 - MA1547, # <u>8</u> Appendix MA1548 - MA1627, # <u>9</u> Appendix MA1628 - MA1693, # <u>10</u> Appendix MA1694 - MA1953, # <u>11</u> Appendix MA1954 - MA2127, # <u>12</u> Appendix MA2128 - MA2206, # <u>13</u> Appendix MA2207 - MA2253, # <u>14</u> Appendix MA2254 - MA2273, # <u>15</u> Appendix MA2274 - MA2333, # <u>16</u> Appendix MA2334 - MA2337, # <u>17</u> Appendix MA2338 - MA2342, # <u>18</u> Appendix MA2343 - MA2346, # <u>19</u> Appendix MA2347 - MA2351, # <u>20</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/26/2010) (2 parts).
D588	REDACTED VERSION of <u>261</u> Answering Brief in Opposition, to Plaintiffs' Motion for Partial Summary Judgment that the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents (CORRECTED VERSION OF D.I. 241) by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
D589	REDACTED VERSION of <u>250</u> Answering Brief in Opposition, to Soitec's Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/26/2010)
D590	REDACTED VERSION of <u>247</u> Answering Brief in Opposition,, to Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of In validity Of The Asserted Aspar Claims by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/26/2010)

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(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

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D591	REDACTED VERSION of <u>254</u> Appendix., to Appendix To Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of Invalidity Of The Asserted Aspar Claims (PA-1103 - PA-1143 by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/26/2010)
D592	REDACTED VERSION of <u>251</u> Appendix., to Appendix to Plaintiffs' Answering Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/26/2010)
D593	REPLY BRIEF re <u>204</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid Reply Brief in Support of Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
D594	DECLARATION re <u>268</u> Reply Brief, Declaration of Marcus T. Hall in Support of Reply Brief in Support of Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
D595	APPENDIX re <u>268</u> Reply Brief, Omnibus Appendix to Plaintiffs' Reply Briefs in Support of Plaintiffs' Daubert Motion and Motions For Partial Summary Judgment (PA-1192 - PA-1261) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1199 - PA-1204, # <u>2</u> Exhibit PA-1205 - PA-1206, # <u>3</u> Exhibit PA-1206.1, # <u>4</u> Exhibit PA-1231 - PA-1237, # <u>5</u> Exhibit PA-1238 - PA-1245, # <u>6</u> Exhibit PA-1246 - PA-1257, # <u>7</u> Exhibit PA-1258 - PA-1261, # <u>8</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
D596	REPLY BRIEF re <u>210</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement Reply Brief in Support of SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D597	REPLY BRIEF re <u>212</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art Reply Brief in Support of SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
D598	REPLY BRIEF re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement Reply Brief in Support of SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
D599	REDACTED VERSION of <u>269</u> Appendix, TO REPLY BRIEF IN SUPPORT OF MEMC's MOTION FOR PARTIAL SUMMARY JUDGMENT OF INVALIDITY OF THE ASSERTED ASPAR PATENT CLAIMS by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix Table of Contents, # <u>2</u> Appendix MA2453_MA2479, # <u>3</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2010)
D600	REDACTED VERSION of <u>273</u> Appendix REPLY BRIEF IN SUPPORT OF MEMC's MOTION FOR SUMMARY JUDGMENT OF NON-INFRINGEMENT by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix Table of Contents, # <u>2</u> Appendix MA2352 - MA2361, # <u>3</u> Appendix MA2362 - MA2371, # <u>4</u> Appendix MA2372 - MA2381, # <u>5</u> Appendix MA2382 - MA2391, # <u>6</u> Appendix MA2392 - MA2399, # <u>7</u> Appendix MA2400 - MA2404, # <u>8</u> Appendix MA2405 - MA2422, # <u>9</u> Appendix MA2423 - MA2425, # <u>10</u> Appendix MA2426 - MA2427, # <u>11</u> Appendix MA2428 - MA2430, # <u>12</u> Appendix MA2431 - MA2440, # <u>13</u> Appendix MA2441 - MA2448, # <u>14</u> Appendix MA2449 - MA2452, # <u>15</u> Appendix MA2452.1 - MA2452.9, # <u>16</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2010)
D601	REDACTED VERSION of <u>267</u> Reply Brief IN SUPPORT OF MEMC's MOTION FOR PARTIAL SUMMARY JUDGMENT OF INVALIDITY OF THE ASSERTED ASPAR PATENT CLAIMS by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 08/03/2010)
D602	REDACTED VERSION of <u>271</u> Reply Brief IN SUPPORT OF MEMC's MOTION FOR SUMMARY JUDGMENT OF NON-INFRINGEMENT by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 08/03/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D603	REDACTED VERSION of <u>274</u> Appendix,, Omnibus Appendix to Plaintiffs' Reply Briefs in Support of Plaintiffs' Daubert Motion and Motions For Partial Summary Judgment (PA-1192 - PA-1198 and PA-1207 - PA-1230 Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 08/06/2010)
D604	REDACTED VERSION of <u>277</u> Reply Brief, in Support of SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
D605	REDACTED VERSION of <u>278</u> Reply Brief,, in Support of SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
D606	REDACTED VERSION of <u>279</u> Reply Brief,, in Support of Plaintiffs' Motion for Partial Summary Judgment That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents (Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
D607	REDACTED VERSION of <u>281</u> Reply Brief, in Support of Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents (Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
D608	REDACTED VERSION of <u>282</u> Reply Brief,, in Support of SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct (Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
D609	NOTICE OF SERVICE of CD of documents MEMC0782194-MEMC0782500 and FH-1 0001 - FH-8 0067 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 09/16/2010)
D610	REDACTED VERSION of <u>301</u> SEALED MOTION for Reconsideration Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 09/24/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D611	REDACTED VERSION of <u>302</u> Declaration, of Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 09/24/2010)
D612	REDACTED VERSION of <u>303</u> Exhibit to a Document Exhibit A to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)
D613	REDACTED VERSION of <u>304</u> Exhibit to a Document Exhibit B to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)
D614	REDACTED VERSION of <u>305</u> Exhibit to a Document Exhibit C to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)
D615	REDACTED VERSION of <u>306</u> Exhibit to a Document Exhibit D to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)
D616	Proposed Pretrial Order [Proposed] Joint Pretrial Order (FILED UNDER SEAL) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit 1 (Sealed), # <u>2</u> Exhibit 2A (Sealed), # <u>3</u> Exhibit 2B (Sealed), # <u>4</u> Exhibit 3A (Sealed), # <u>5</u> Exhibit 3B (Sealed), # <u>6</u> Exhibit 4A (Sealed), # <u>7</u> Exhibit 4B (Sealed), # <u>8</u> Exhibit 4C (Sealed), # <u>9</u> Exhibit 5A (Sealed), # <u>10</u> Exhibit 5B (Sealed), # <u>11</u> Exhibit 6A (Sealed), # <u>12</u> Exhibit 6B (Sealed), # <u>13</u> Exhibit 7A (Sealed), # <u>14</u> Exhibit 7B (Sealed), # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 10/07/2010)
D617	Proposed Voir Dire by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 10/08/2010)
D618	VERDICT SHEET by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 10/08/2010)
D619	Proposed Voir Dire by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/08/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

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D620	VERDICT SHEET by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/08/2010)
D621	Proposed Jury Instructions by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 10/08/2010)
D622	Proposed Jury Instructions by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 10/08/2010)
D623	REDACTED VERSION of <u>315</u> Proposed Pretrial Order., Redacted Version of [Proposed] Joint Pretrial Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2A, # <u>3</u> Exhibit 2B, # <u>4</u> Exhibit 3A, # <u>5</u> Exhibit 3B, # <u>6</u> Exhibit 4A, # <u>7</u> Exhibit 4B, # <u>8</u> Exhibit 4C, # <u>9</u> Exhibit 5A, # <u>10</u> Exhibit 5B, # <u>11</u> Exhibit 6A, # <u>12</u> Exhibit 6B, # <u>13</u> Exhibit 7A, # <u>14</u> Exhibit 7B, # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 10/13/2010)
D624	MEMORANDUM OPINION. Signed by Judge Sue L. Robinson on 10/13/2010. (nmf) (Entered: 10/13/2010)
D625	ORDER denying <u>141</u> Motion for Discovery; denying <u>186</u> Motion in Limine; granting in part and denying in part <u>187</u> Motion for Partial Summary Judgment; granting <u>197</u> Motion for Summary Judgment ; granting <u>199</u> Motion for Summary Judgment ; granting <u>202</u> Motion for Partial Summary Judgment; denying <u>204</u> Motion for Partial Summary Judgment; denying <u>206</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>208</u> Motion for Partial Summary Judgment; denying <u>210</u> Motion for Partial Summary Judgment; denying <u>212</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>213</u> Motion for Partial Summary Judgment. Signed by Judge Sue L. Robinson on 10/13/2010. (nmf) (Entered: 10/13/2010)
D626	MEMORANDUM ORDER re: claim construction. Signed by Judge Sue L. Robinson on 10/13/2010. (nmf) (Entered: 10/13/2010) ORAL ORDER by Judge Sue L. Robinson on 10/14/2010 that the responses to the issues raised in the exhibits to the joint pre-trial order are to be stricken from the record. (These filings, formerly D.I. Nos. 318 and 323 have been deleted from the docket.) (nmf) (Entered: 10/14/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D627	AMENDED ORDER denying <u>141</u> Motion for Discovery; denying <u>186</u> Motion in Limine; granting in part and denying in part <u>187</u> Motion for Partial Summary Judgment; granting <u>197</u> Motion for Summary Judgment ; granting <u>199</u> Motion for Summary Judgment ; granting <u>202</u> Motion for Partial Summary Judgment; denying <u>204</u> Motion for Partial Summary Judgment; denying <u>206</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>208</u> Motion for Partial Summary Judgment; denying <u>210</u> Motion for Partial Summary Judgment; denying <u>212</u> Motion for Partial Summary Judgment; "granting" <u>213</u> Motion for Partial Summary Judgment. Signed by Judge Sue L. Robinson on 10/14/2010. (nmf) (Entered: 10/14/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Final Pretrial Conference held on 10/14/2010. (Court Reporter V. Gunning.) (nmf) (Entered: 10/15/2010) SO ORDERED, re <u>315</u> Proposed Pretrial Order. Signed by Judge Sue L. Robinson on 10/14/2010. (nmf) (Entered: 10/15/2010)
D628	MOTION for Reargument re <u>327</u> Memorandum and Order - Reargument of Claim Construction of One Claim Term of U.S. Patent 6,809,009 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 10/18/2010)
D629	SECOND AMENDED ORDER re: <u>325</u> denying <u>141</u> Motion for Discovery; denying <u>186</u> Motion in Limine; granting in part and denying in part <u>187</u> Motion for Partial Summary Judgment; granting <u>197</u> Motion for Summary Judgment ; granting <u>199</u> Motion for Summary Judgment **with respect to the '484 patent and with respect to its current process, and denied in other respects; granting <u>202</u> Motion for Partial Summary Judgment; denying <u>204</u> Motion for Partial Summary Judgment; denying <u>206</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>208</u> Motion for Partial Summary Judgment; denying <u>210</u> Motion for Partial Summary Judgment; denying <u>212</u> Motion for Partial Summary Judgment; granting <u>213</u> Motion for Partial Summary Judgment. Signed by Judge Sue L. Robinson on 10/19/2010. (nmf) (Entered: 10/19/2010)
D630	MEMORANDUM ORDER granting <u>329</u> MOTION for Reargument re <u>327</u> Memorandum and Order - Reargument of Claim Construction of One Claim Term of U.S. Patent 6,809,009. Signed by Judge Sue L. Robinson on 10/19/2010. (nmf) (Entered: 10/19/2010)
D631	STIPULATION MEMC's Declaratory Judgment counterclaim asserting invalidity of United States Reissued Patent No. 39,484 in Civil Action No. 1:08-292-SLR is dismissed without prejudice by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (nmf,). (Entered: 10/21/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D632	STIPULATION of Fact re <u>331</u> Memorandum and Order, <u>327</u> Memorandum and Order, <u>325</u> Memorandum Opinion by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 10/21/2010)
D633	Letter to The Honorable Sue L. Robinson from Denise Seastone Kraft regarding Mutually agreed upon narrowing of the issues for trial - re <u>333</u> Stipulation, <u>332</u> Stipulation,. (Kraft, Denise) (Entered: 10/21/2010) CORRECTING ENTRY: The pdf of D.I. <u>332</u> has been replaced with the correct pdf of the stipulation per request of filer. (nmf) (Entered: 10/22/2010) SO ORDERED, re <u>333</u> Stipulation filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a LEnergie Atomique, <u>332</u> Stipulation, filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a LEnergie Atomique. Signed by Judge Sue L. Robinson on 10/22/2010. (nmf) (Entered: 10/22/2010)
D634	Voir Dire Questions. Read in Open Court 10/25/2010.(nmf) (Entered: 10/25/2010)
D635	Preliminary Jury Instructions. Read in Open Court 10/25/2010. (nmf) (Entered: 10/25/2010) Minute Entry for proceedings held before Judge Sue L. Robinson: Jury Trial Day 1 held on 10/25/2010. (Court Reporter Valerie Gunning, Brian Gaffigan.) (dlk) (Entered: 10/26/2010)
D636	PLAINTIFF'S BENCH MEMORANDUM. Filed in Court 10/26/2010. (nmf) (Entered: 10/26/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial (Day 2) held on 10/26/2010. (Court Reporter Valerie Gunning, Kevin Maurer.) (dlk) (Entered: 10/26/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial - Day 3, held on 10/27/2010. (Court Reporter Valerie Gunning/Kevin Maurer.) (nms) (Entered: 10/27/2010)
D637	STATEMENT -- BENCH MEMORANDUM SUPPORTING MEMC'S PROFFER OF ADMISSIONS BY SOITEC IN PRIOR LAWSUIT INVOLVING THE '564 PATENT submitted at trial by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit A)(Rogowski, Patricia) (Entered: 10/28/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial - Day 4 held on 10/28/2010. (Court Reporter Valerie Gunning/Kevin Maurer.) (nms) (Entered: 11/01/2010)
D638	Final Jury Instructions read in open Court by Judge Robinson. (lid) (Entered: 11/01/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial held on 11/1/2010. (DAY 5) (Court Reporter V. Gunning.) (lid) (Entered: 11/02/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial completed on 11/2/2010. (DAY 6) (Court Reporter V. Gunning.) (lid) (Entered: 11/02/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

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	D639	REDACTED VERSION OF <u>342</u> Jury Verdict. (lid) (Entered: 11/02/2010)
	D640	STATEMENT Bench Memorandum in Support of Plaintiffs' Motion For Judgment as a Matter of Law of No Unenforceability of the '009 Patent Due To Inequitable Conduct submitted at trial by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 11/02/2010)
	D641	ANSWERING BRIEF in Opposition re <u>301</u> SEALED MOTION for Reconsideration Request to Modify Protective Order (MEMC'S OPPOSITION TO PLAINTIFFS' MOTION FOR REARGUMENT RE: MODIFICATION OF THE PROTECTIVE ORDER) filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 11/22/2010. (Attachments: # <u>1</u> Exhibit 1 through 5, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 11/12/2010)
	D642	JUDGMENT in favor of defendant MEMC Electronic Materials, Inc. and against plaintiffs S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat A LEnergie Atomique et aux Energies Alternatives as to the 812 patent. IT IS FURTHER ORDERED that judgment be and is hereby entered in favor of plaintiffs S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat A LEnergie Atomique et aux Energies Alternatives and against defendant MEMC Electronic Materials, Inc. as to the 009 patent. Signed by Judge Sue L. Robinson on 11/15/2010. (nmf) (Entered: 11/15/2010)
	D643	STIPULATION Setting Post-Trial Briefing Schedule re <u>348</u> Judgment,, by Commissariat a LEnergie Atomique, MEMC Electronic Materials Inc., SOITEC Silicon On Insulator Technologies SA. (Rogowski, Patricia) (Entered: 11/15/2010)
	D644	MOTION for Reargument re <u>348</u> Judgment,, (MEMC'S MOTION FOR REARGUMENT OF THE COURTS ORDER RE: THE UNENFORCEABILITY OF THE 009 PATENT) - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1)(Rogowski, Patricia) (Entered: 11/16/2010) SO ORDERED- re <u>349</u> Stipulation. Set POST TRIAL Briefing Schedule: (Opening Brief due 12/8/2010., Answering Brief due 12/29/2010., Reply Brief due 1/12/2010.). Signed by Judge Sue L. Robinson on 11/17/2010. (lid) (Entered: 11/17/2010)
	D645	MOTION for Leave to File Reply in Support of Plaintiff's Motion for Reargument - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/23/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D646	OPENING BRIEF in Support re <u>301</u> SEALED MOTION for Reconsideration Request to Modify Protective Order, <u>351</u> MOTION for Leave to File Reply in Support of Plaintiff's Motion for Reargument filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 12/10/2010. (Attachments: # <u>1</u> Appendix A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/23/2010)
D647	STIPULATION TO EXTEND TIME Respond to MEMC's Motion for Reargument of the Court's Order Re: Unenforceability of the '009 Patent to December 3, 2010 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 11/24/2010) SO ORDERED- re <u>353</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: re <u>350</u> MOTION for Reargument re <u>348</u> Judgment,. (Answering Brief due 12/3/2010.). Signed by Judge Sue L. Robinson on 11/30/2010. (lid) (Entered: 11/30/2010)
D648	STIPULATION TO EXTEND TIME to file Motions and Opening Post-Trial Briefs to December 13, 2010 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/03/2010)
D649	REPLY BRIEF re <u>350</u> MOTION for Reargument re <u>348</u> Judgment,. (MEMCS MOTION FOR REARGUMENT OF THE COURTS ORDER RE: THE UNENFORCEABILITY OF THE '009 PATENT) Plaintiffs' Opposition to MEMC's Motion For Reargument of the Court's Order Re: The Unenforceability of the '009 Patent filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 12/03/2010) SO ORDERED- re <u>354</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: (POST TRIAL Opening Brief due 12/13/2010.). Signed by Judge Sue L. Robinson on 12/6/2010. (lid) (Entered: 12/06/2010)
D650	EXHIBIT re <u>355</u> Reply Brief, Exhibit B to Plaintiffs' Opposition to MEMC's Motion For Reargument of the Court's Order Re: The Unenforceability of the '009 Patent by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/06/2010)
D651	ANSWERING BRIEF in Opposition re <u>351</u> MOTION for Leave to File Reply in Support of Plaintiff's Motion for Reargument filed by MEMC Electronic Materials Inc.. Reply Brief due date per Local Rules is 12/20/2010. (Rogowski, Patricia) (Entered: 12/10/2010)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D652	STIPULATION TO EXTEND TIME Stipulation and Order for Plaintiffs to file Motions and Opening Post-Trial Briefs to December 14, 2010 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/13/2010)
D653	MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/13/2010)
D654	OPENING BRIEF in Support re <u>359</u> MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL filed by MEMC Electronic Materials Inc.. Answering Brief/Response due date per Local Rules is 12/30/2010. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 12/13/2010)
D655	MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 12/14/2010)
D656	OPENING BRIEF in Support re <u>361</u> MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 1/3/2011. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 12/14/2010)
D657	MOTION For Injunctive Relief Plaintiffs' Motion For Injunctive Relief And To Lift Stay on Damages Discovery - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 12/14/2010)
D658	STIPULATION TO EXTEND TIME due date for Answering and Reply Post-Trial Briefs to January 7, 2011 for Answering Brief and January 21, 2011 for Reply Brief - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/15/2010) SO ORDERED- re <u>365</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: (Answering Post trial Brief due 1/7/2011., Reply post trial Brief due 1/21/2011.). Signed by Judge Sue L. Robinson on 12/16/2010. (lid) (Entered: 12/17/2010)
D659	STIPULATION TO EXTEND TIME Post-Trial Answering Briefs to January 12, 2011 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 01/06/2011)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
D660	NOTICE of Appearance by Aleine Michelle Porterfield on behalf of Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc. (Attachments: # <u>1</u> Certificate of Service)(Porterfield, Aleine) (Entered: 01/07/2011)
D661	Joint STIPULATION TO EXTEND TIME Post-trial Answering Briefs and Post-trial Reply Briefs to January 14, 2011 and January 28, 2011 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 01/12/2011)
D662	ANSWERING BRIEF in Opposition re <u>359</u> MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..Reply Brief due date per Local Rules is 1/24/2011. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 01/14/2011).
D663	ANSWERING BRIEF in Opposition re <u>361</u> MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial (MEMCS ANSWERING BRIEF IN OPPOSITION TO PLAINTIFFS RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL) filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 1/24/2011. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/14/2011).
D664	DECLARATION re <u>378</u> Answering Brief in Opposition, (DECLARATION OF ROBERT M. EVANS, JR. IN SUPPORT OF MEMCS OPPOSITION TO PLAINTIFFS RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL) by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/14/2011)
D665	REDACTED VERSION of <u>376</u> Answering Brief in Opposition, to Plaintiffs' Motion for Injunctive Relief and to Lift Stay on Damages Discovery by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/20/2011)
D666	REDACTED VERSION of <u>377</u> Appendix to MEMC's Answering Brief in Opposition to Plaintiffs' Motion for Injunctive Relief and to Lift Stay on Damages Discovery by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1-7, # <u>2</u> Exhibit 8, # <u>3</u> Exhibit 9, # <u>4</u> Exhibit 10, # <u>5</u> Exhibit 11, # <u>6</u> Exhibit 12-13, # <u>7</u> Exhibit 14, # <u>8</u> Exhibit 15, # <u>9</u> Exhibit 16, # <u>10</u> Exhibit 17, # <u>11</u> Exhibit 18, # <u>12</u> Exhibit 19, # <u>13</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/20/2011)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)		APPLICANT(S): Nguyet-Phuong Nguyen et al.

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)
D667	Joint STIPULATION TO EXTEND TIME of Post-Trial Reply Briefs to Tuesday, February 1, 2011 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 01/28/2011)
D668	Joint STIPULATION TO EXTEND TIME of Post-Trial Reply Briefs to Friday, February 4, 2011 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 01/31/2011)
D669	REDACTED VERSION of <u>364</u> Opening Brief in Support,,,, Redacted Version of Opening Brief In Support of Plaintiffs' Motion For Injunctive Relief And To Lift Stay on Damages Discovery by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Exhibit E, # <u>6</u> Exhibit F, # <u>7</u> Exhibit G, # <u>8</u> Exhibit H, # <u>9</u> Exhibit I, # <u>10</u> Exhibit J, # <u>11</u> Exhibit K, # <u>12</u> Exhibit L, # <u>13</u> Exhibit M, # <u>14</u> Exhibit N, # <u>15</u> Exhibit O, # <u>16</u> Exhibit P, # <u>17</u> Exhibit Q, # <u>18</u> Exhibit R, # <u>19</u> Exhibit S)(Kraft, Denise) (Entered: 02/02/2011)
D670	REPLY BRIEF re <u>359</u> MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 02/04/2011)
D671	REPLY BRIEF re <u>361</u> MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 02/04/2011)
D672	DECLARATION re <u>387</u> Reply Brief, Declaration of Michael L. Brody in Support of Reply Brief In Support of Plaintiffs' Renewed Motion For Judgment as a Matter of Law or In The Alternative For a New Trial by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 02/04/2011)
D673	MOTION to Strike <u>386</u> Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC'S Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 02/08/2011)

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FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40 (BIF116533US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 3, 2007	GROUP ART UNIT 2813
(use several sheets if necessary)	APPLICANT(S): Nguyet-Phuong Nguyen et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.	
D674	OPENING BRIEF in Support re <u>390</u> MOTION to Strike <u>386</u> Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) MOTION to Strike <u>386</u> Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 2/25/2011. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 02/08/2011)	
D675	DECLARATION re <u>391</u> Opening Brief in Support,, Declaration of Marcus T. Hall in Support of Plaintiffs' Opening Brief in Support of Motion to Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 02/08/2011)	
D676	REDACTED VERSION of <u>389</u> Reply Brief, Redacted Version of Reply Brief in Support of Plaintiffs' Motion For Injunctive Relief And To Lift Stay on Damages Discovery by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 02/09/2011)	

EXAMINER /Daniel Luke/	DATE CONSIDERED 08/09/2011
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